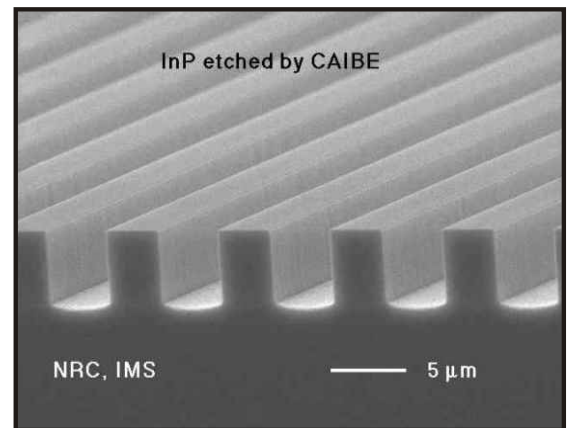
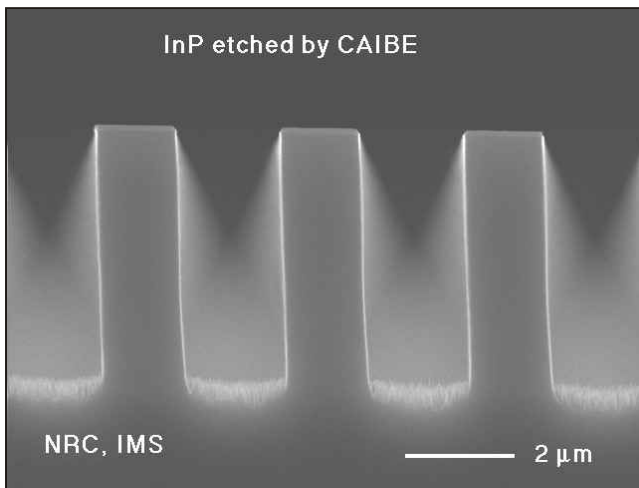
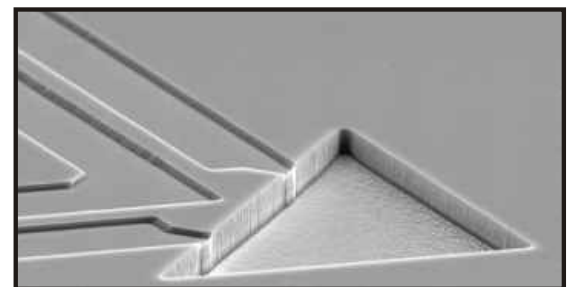
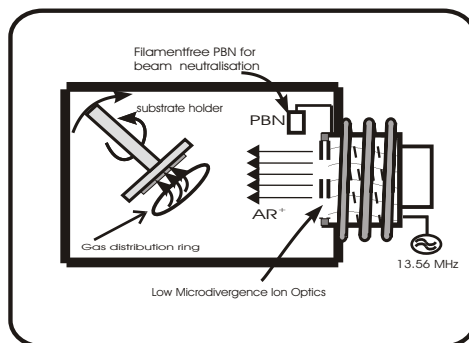


Ionfab Data

InP/ InGaAsP/ InP CAIBE



Courtesy of National Research Council, Ottawa
(Dr B. Lamontagne);
5 μm deep anisotropic etch through InP/ InGaAsP/ InP



turning mirror etched in InP by CAIBE

Technology:

- Etch Mode: CAIBE
- Cl₂/Ar-Process
- Rotating substrate with adjustable tilt
- Ion source: 15 cm, 13.56 MHz driven
- Ion Optics: Low Divergence
- Beam Neutralisation: filamentfree PBN

Results:

- mask: SiO₂
- selectivity : up to 30 :1
- smooth walls
- aspect ratio: up to 10 : 1 (at 15 μm depth)
- suitable for low loss single- and multi mode
- turning mirrors (0.3 dB per mirror)

Ionfab 300 Plus

